

Electron-hole recombination mechanism in halide perovskites

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A research team led by Prof. Zhao Jin from Department of Physics,

University of Science and Technology of China (USTC) of the Chinese Academy of Sciences found low-frequency lattice phonons in halide perovskites resulting in high defect tolerance toward electron-hole recombination with their independently-developed software, Hefei-NAMD. The study published in *Science Advances*.

Solar cells have been wildly used in various livelihood or industrial applications, while the efficiency and durability of solar energy semiconductors still harass manufacturers. Defects in semiconducting materials form electron-hole (e-h) [recombination](#) centers detrimental to solar conversion efficiency. This is an important scientific issue in this field.

As early as the 1950s, the scientists Shockley, Read and Hall proposed the famous Shockley-Read-Hall (SRH) model via which [defect](#) states in the band gap form e-h recombination centers. And for decades, the abstract model has been adapted by many scientists in the semiconducting field. However, it does not account for the electron-phonon coupling which is the key for e-h recombination by nonradiative processes.

In this study, the researchers investigated the e-h recombination processes due to native point defects in methylammonium lead halide (MAPbI₃) perovskites using [ab initio](#) nonadiabatic molecular dynamics and taking factors in count precisely such as electron-phonon interactions, energy levels, nuclear velocity, decoherence effects and carrier concentration. They found that charge recombination in MAPbI₃ was not enhanced regardless of whether the defects introduce a shallow or deep band state, which meant the SRH theory lapsed.

Though analyzing the [electron-phonon coupling](#) quantitatively, they demonstrated that the photogenerated carriers are only coupled with low-frequency phonons and electron and hole states overlap weakly, which

explained why MAPbI_3 still shows high solar conversion efficiency with many defects.

These findings are significant in the future design of functional semiconducting materials for solar energy conversion.

More information: Weibin Chu et al. Low-frequency lattice phonons in halide perovskites explain high defect tolerance toward electron-hole recombination, *Science Advances* (2020). [DOI: 10.1126/sciadv.aaw7453](https://doi.org/10.1126/sciadv.aaw7453)

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